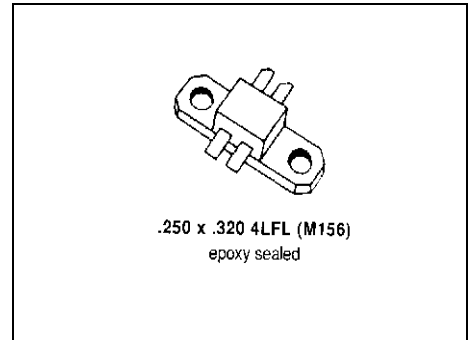


MS1579

**RF & MICROWAVE TRANSISTORS
TV LINEAR APPLICATIONS**

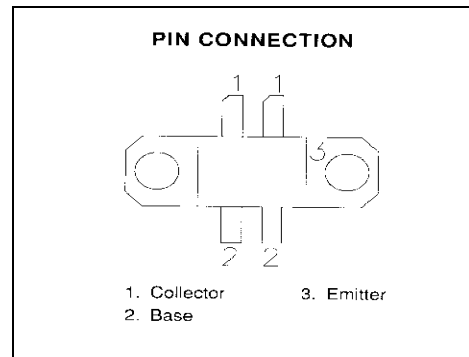
Features

- 470 - 860 MHz
- 25 VOLTS
- CLASS A OPERATION
- INTERNAL INPUT MATCHING
- P_{OUT} = 14 WATTS
- G_p = 8.5 dB MINIMUM
- COMMON EMITTER CONFIGURATION



DESCRIPTION:

The MS1579 is a gold metallized, epitaxial silicon NPN transistor designed for Class A, UHF and Band IV, V television transmitters applications. Diffused emitter ballast resistors ensure long term reliability under Class A linear operation.



ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	45	V
V _{CEO}	Collector-Emitter Voltage	25	V
V _{EBO}	Emitter-Base Voltage	4.0	V
P _{DISS}	Power Dissipation	65	W
I _c	Device Current	5.2	A
T _J	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Thermal Data

R _{TH(J-C)}	Thermal Resistance Junction-case	2.5	°C/W
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ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

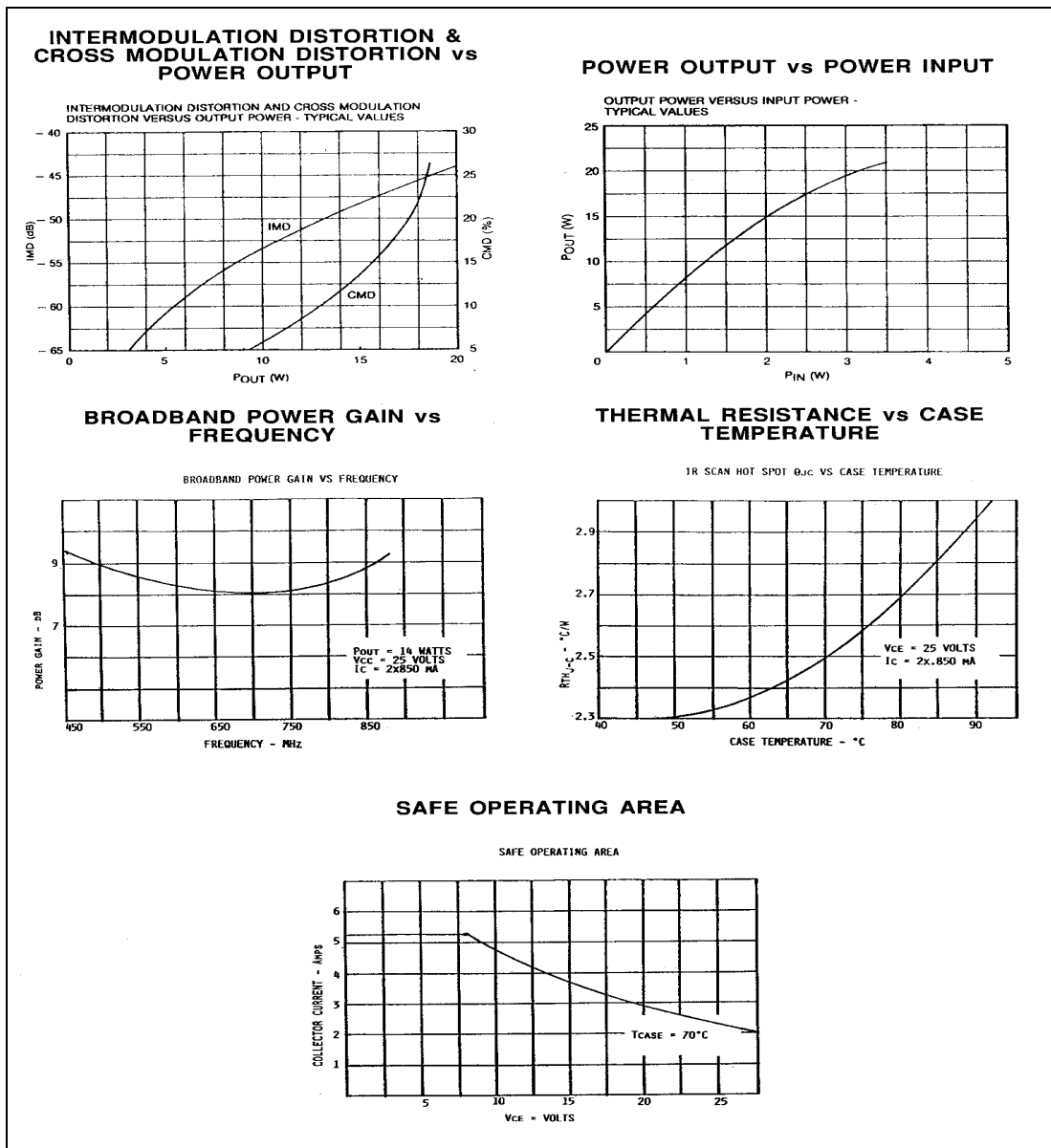
Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV _{CBO}	I _C = 20 mA	I _E = 0 mA	45	---	---	V
BV _{CEO}	I _C = 40 mA	I _B = 0 mA	25	---	---	V
BV _{EBO}	I _E = 5 mA	I _C = 0 mA	3.0	---	---	V
HFE	V _{CE} = 20 V	I _C = 0.5 A	10	---	200	---

DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P _{OUT}	f = 845 MHz	P _{IN} = 2.0	V _{CE} = 25 V	14	---	---	W
G _P	P _{OUT} = 14 W	P _{IN} = 2.0	V _{CE} = 25 V	8.5	---	---	dB
IMD ₃	P _{OUT} = 14 W	P _{IN} = 2.0	V _{CE} = 25 V	---	-47	---	dBc
C _{OB}	f = 1 MHz	V _{CB} = 25 V		---	---	20	pf

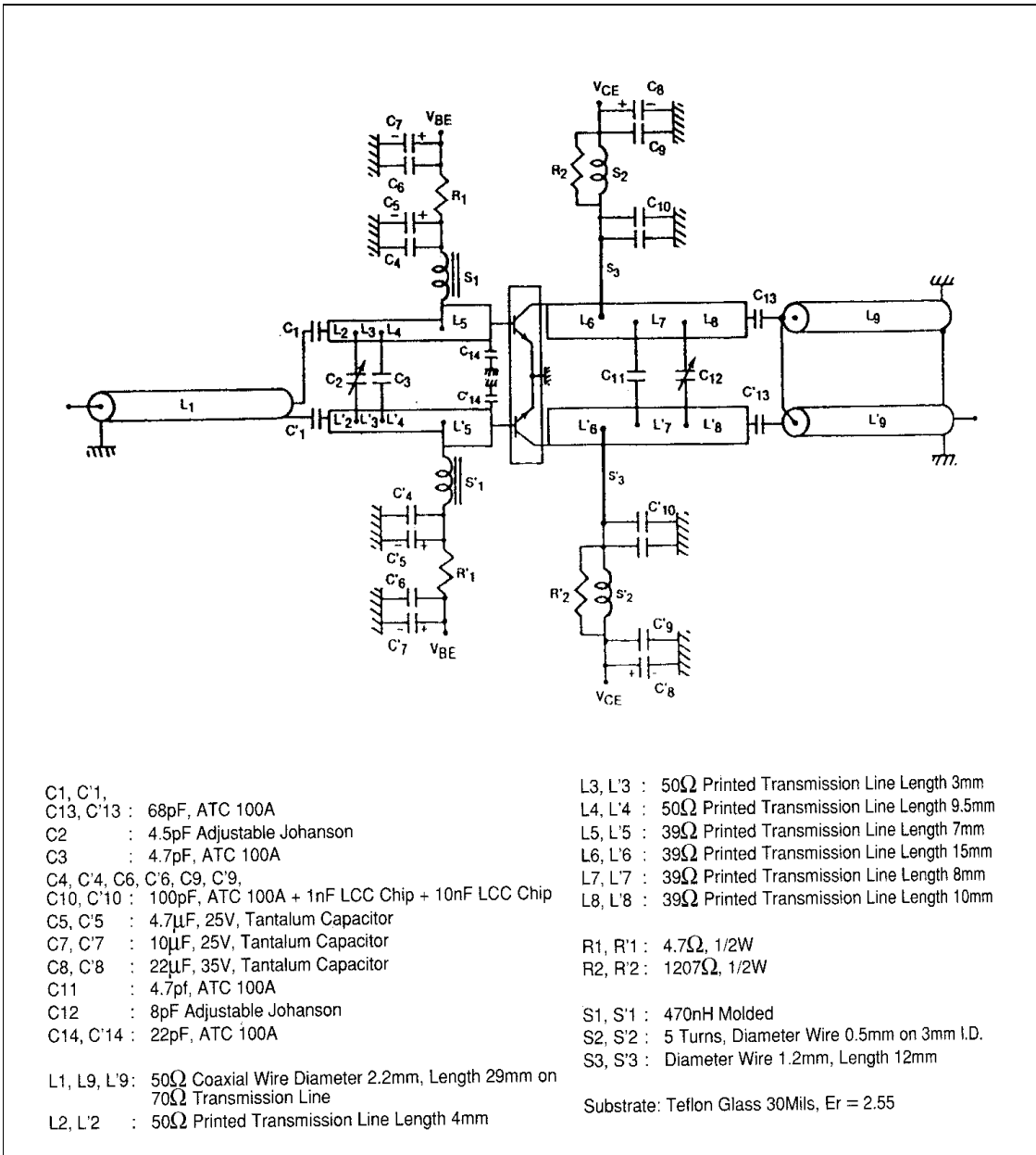
Conditions: V_{CE} = 25 V I_{CQ} = 2 x 850 mA

TYPICAL PERFORMANCE





TEST CIRCUIT



PACKAGE MECHANICAL DATA

